

HA166132FP, HA166134FP HA166132T, HA166134T

Read/Write Amplifier for Hard Disk Drive



Preliminary
Rev. 1
Nov. 1991

The HA166132FP, HA166134FP, HA166132T and HA166134T are read/write amplifiers designed for use with thin film heads. They have the following functions and features.

Functions

- Read amplifier circuit
- Write driver circuit
- Write error detection circuit
- Constant write current setup circuit

Features

- Single power supply +5 V
- Low power
 - read: 150 mW (typ)
 - idle: 5 mW (typ)
- Low Noise: 0.7 nV/ $\sqrt{\text{Hz}}$ (typ)
- Read amplifier has high differential voltage gain : 250 V/V (typ)
- Built-in current and voltage monitors
- TTL compatible interface
- Emitter-follower read amplifier outputs
- Input capacitance: 22 pF (typ)
- Write current range: 10 to 30 mA

Ordering Information

Type	Channel	Package
HA166132FP	2	FP-16DA
HA166134FP	4	FP-20DA
HA166132T	2	TTP-20DA
HA166134T	4	TTP-20DA



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Pin Arrangements

• HA166132FP

GND	1	16	CS
H0X	2	15	R/W
H0Y	3	14	WC
H1X	4	13	RDY
H1Y	5	12	RDX
V _{CC}	6	11	HS0
NC	7	10	V _{CC}
WUS	8	9	WDI

(Top view)

• HA166132T

GND	1	20	CS
H0X	2	19	R/W
H0Y	3	18	WC
NC	4	17	RDY
NC	5	16	RDX
H1X	6	15	NC
H1Y	7	14	HS0
NC	8	13	V _{CC}
NC	9	12	WDI
V _{CC}	10	11	WUS

(Top view)

• HA166134FP

GND	1	20	CS
H0X	2	19	R/W
H0Y	3	18	WC
H1X	4	17	RDY
H1Y	5	16	RDX
H2X	6	15	HS0
H2Y	7	14	HS1
H3X	8	13	V _{CC}
H3Y	9	12	WDI
V _{CC}	10	11	WUS

(Top view)

• HA166134T

GND	1	20	CS
H0X	2	19	R/W
H0Y	3	18	WC
H1X	4	17	RDY
H1Y	5	16	RDX
H2X	6	15	HS0
H2Y	7	14	HS1
H3X	8	13	V _{CC}
H3Y	9	12	WDI
V _{CC}	10	11	WUS

(Top view)

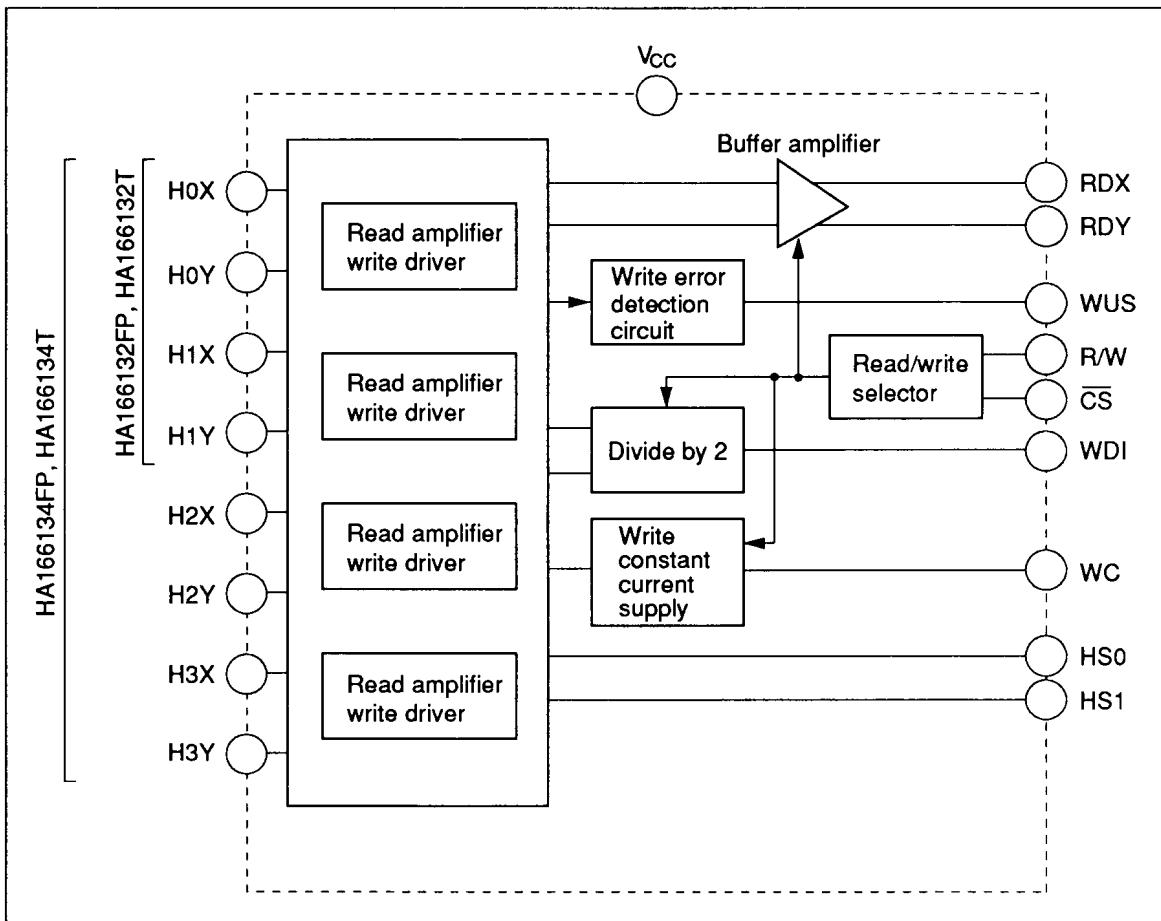
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Pin Description

Symbol	Name	Description
RDX, RDY	Read amplifier output	Differential output pins for the read amp. The signal read out from the head coil is amplified and provided on these pins.
R/W	R/W switch	Mode select switch for changing over the bias condition of the head coil A low level selects the write mode, while a high level selects the read mode.
CS	Chip select	When this line is set high, the circuit goes into the standby state, a low power state. When this line is low, the chip is active.
HS0	Head select 0	Input pins for head select signals. The combination of these signals selects one head from head 0 to head 3.
HS1	Head select 1	Refer to the head select table.
H0X, H0Y	Head 0X, 0Y	These pins are connected to the R/W head coil of channel 0.
H1X, H1Y	Head 1X, 1Y	These pins are connected to the R/W head coil of channel 1.
H2X, H2Y	Head 2X, 2Y	These pins are connected to the R/W head coil of channel 2.
H3X, H3Y	Head 3X, 3Y	These pins are connected to the R/W head coil of channel 3.
WC	Write current setting	Write current setting pin. The write current is defined by the equation below by connecting the external resistance R_{WC} between this pin and GND. $\text{Write current [mA]} = K/R_{WC} [\text{k}\Omega]$
WDI	Write data input	Write data input pin. The signal is devided in the IC, and drives the write driver.
WUS	Write error detection circuit	A high level output indicates the write error detection conditions. WUS is high under the following conditions: <ol style="list-style-type: none"> 1. Head open 2. Head short 3. Write current too small. 4. WDI input frequency too low.
V _{CC}	5 V	5 V power supply
GND	Ground	Ground pins

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Block Diagram



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Rating	Unit	Applicable Terminal
Supply voltage	V5	-0.3 to +6.0	V	V _{CC}
Write current	I _W	35	mA	
Interface input voltage	V _{IN}	-0.3 to V ₅ +0.3	V	HS0, HS1, WDI, R/W, CS
WUS voltage	V _{WUS}	6.0	V	WUS
WUS output current	I _{WUS}	12	mA	WUS
Read data output current	I _{RO}	-10	mA	RDX, RDY
Operating temperature	T _{opr}	0 to +70	°C	
Storage temperature	T _{stg}	-55 to +125	°C	

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Power Supply ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Supply voltage range	V_{CC}	4.75	5.0	5.25	V	
+5 V supply current	I _S	—	33	45	mA	Read mode $V_{CC} = 5.25 \text{ V}$
			$21 + I_W$	$30 + I_W$		Write mode $V_{CC} = 5.25 \text{ V}$
			1.1	3		Idle mode $V_{CC} = 5.25 \text{ V}$

Electrical Characteristics ($V_{CC} = 5 \text{ V}$, $T_a = 25^\circ\text{C}$ unless otherwise specified)

Digital Input

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Low level input voltage	V_{IL}	-0.3	—	0.8	V	
Low level input current	I_{IL}	-100	—	—	μA	$V_{IL} = 0.8 \text{ V}$
High level input voltage	V_{IH}	2.0	—	$V_{CC} + 0.3$	V	
High level input current	I_{IH}	—	100	100	μA	$V_{IH} = 2.0 \text{ V}$
Read/write transition time	t_{RW}	—	1000	1000	ns	
Write/read transition time	t_{WR}	—	1500	1500	ns	
Head select switching delay time	t_{HS}	—	1500	1500	ns	Read or write mode
Chip disable transition time	t_{IRW}	—	12	12	μs	R/W to Idle or Idle to R/W

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Write Fault Detection

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Low level US voltage	V _{OL}	—	—	0.5	V	I _{OL} = 8 mA
High level US current	I _{OH}			100	μA	V _{OH} = 5.0 V
Unsafe to safe delay time	t _{d2}			1.0	μs	
Safe to unsafe delay time	t _{d1}	0.8		6.0		

Head Select Table

HS1	HS0	Head Selected
L	L	0
	H	1
H	L	2
	H	3

Mode Select Table

CS	R/W	Mode
L	L	Write
	H	Read
H	L	Idle
	H	

Read Amplifier

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Differential voltage gain	Avd	220	250	280	V/V	f = 300 kHz
Bandwidth	V _W	40	70	—	MHz	—3 dB
Input noise voltage	V _n	—	0.7	0.85	nV/√Hz	f ≤ 15 MHz, Inputs shorted
Common mode rejection ratio	CMRR	60	80	—	dB	
Power supply stability	PSRR	45	60	—		V _{CC} ±100 mVpp, f = 5 MHz
Channel separation	Sep	60	80	—		Vin = 100 mVpp on unselected channels and Vin = 0 mVpp on selected channels, f = 5 MHz
Output offset voltage	V _o	—300	—	300	mV	Inputs shorted
Differential input impedance	R _{in}	—	1.1	—	kΩ	f = 300 kHz
			0.85			f = 5 MHz
Common mode output voltage	V _{ocm}	2.0	2.5	3.0	V	
Output source current	I _{ODR}	—	—10	—	mA	
Output sink current	I _{OSDR}	1.7	2.2			

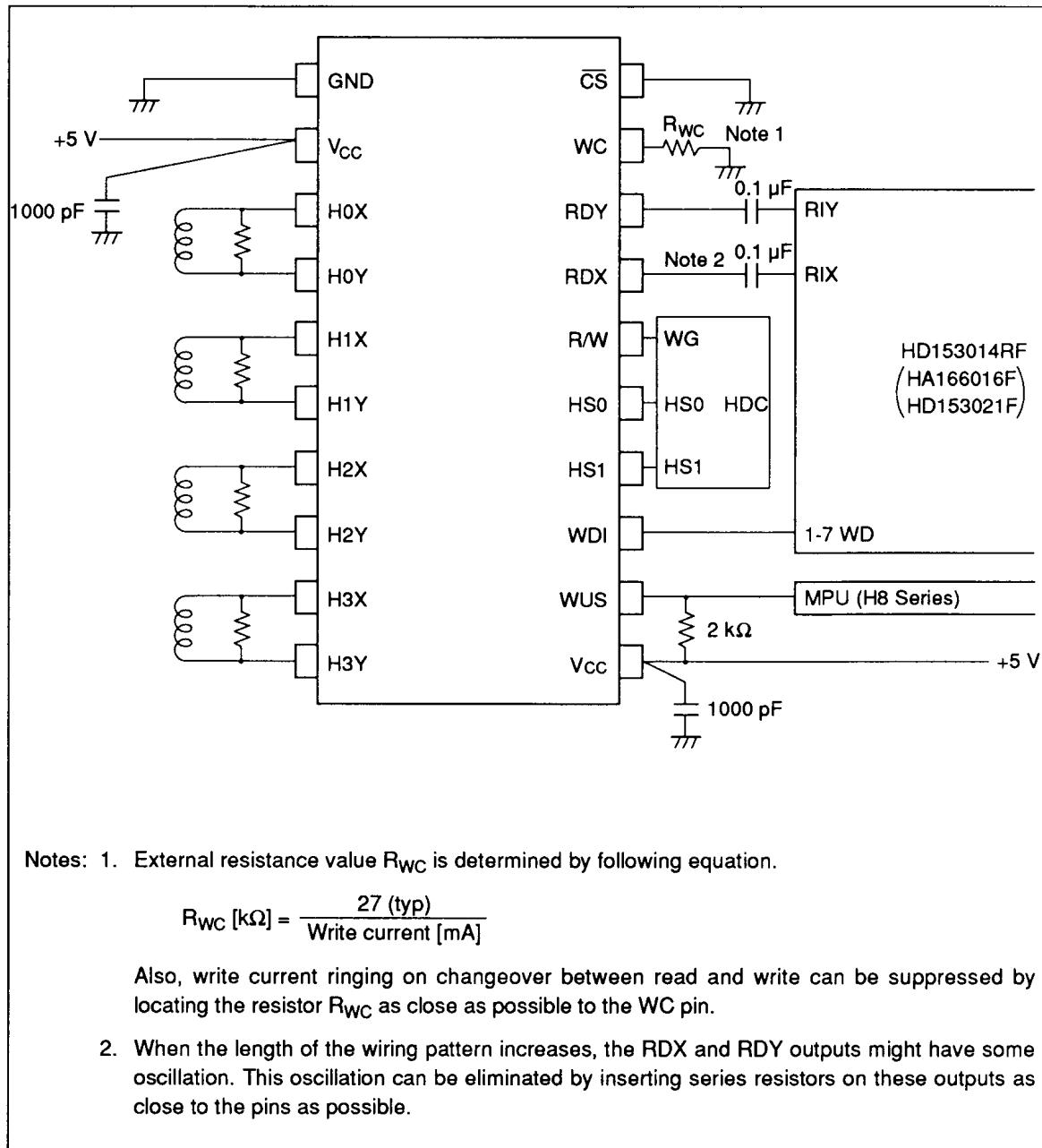
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Write Driver

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Write current setting range	I_W	10	—	30	mA	
Head current rise time	t_{hex}	—	6	20	ns	$L_h = 0 \mu H$, $R_h = 0 \Omega$, 10% to 90% point
Head current switching delay time	t_{d3}	—	12	35	—	$R_h = 0 \Omega$, $L_h = 0 \mu H$, from 50% point
Head current switching symmetry	t_{d4}	—	—	1	—	WDI duty cycle = 50%, rise/fall time = 1 ns
WDI minimum input frequency	f_w	1.8	—	—	MHz	WUS = low
Head current gain	I_h/I_{WC}	—	20	—	—	Head current/ I_{WC}
WC output voltage	V_{WC}	—	1.35	—	V	
Write current determination coefficient	K	24.8	27	29.2	—	

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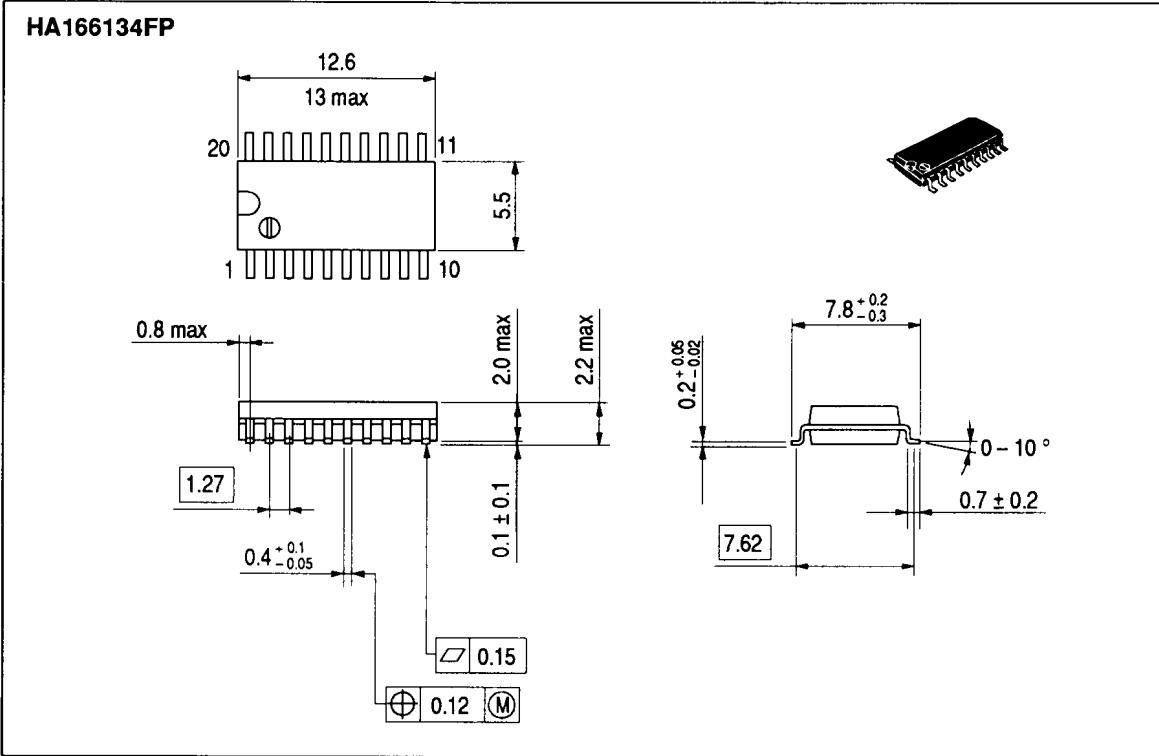
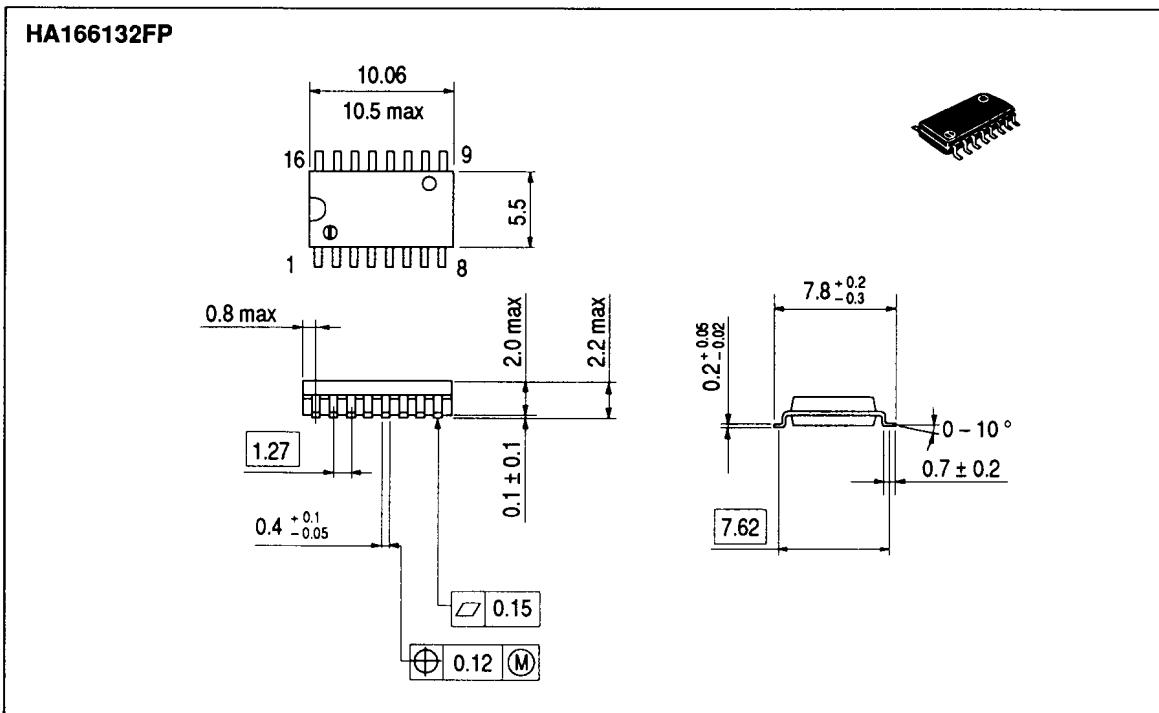
Application Circuit Example



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Package Dimensions

Unit: mm

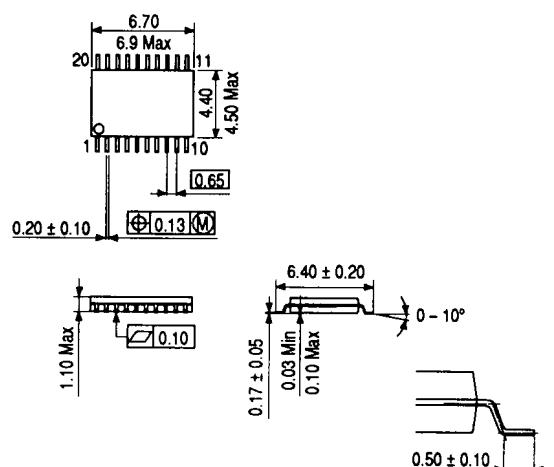


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Package Dimensions (cont)

Unit: mm

- HA166132T
- HA166134T



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